3-V TO 5.5-V MULTICHANNEL RS-232 LINE DRIVER/RECEIVER WITH ±15-kV ESD PROTECTION

Check for Samples: TRSF3223E

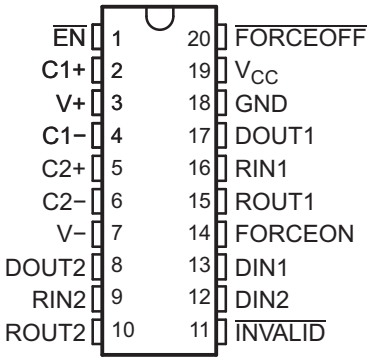
FEATURES

- **ESD Protection for RS-232 Bus Pins**
  - **±15-kV Human-Body Model (HBM)**
  - **±8-kV IEC 61000-4-2, Contact Discharge**
  - **±15-kV IEC 61000-4-2, Air-Gap Discharge**
- **Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards**
- **Operates With 3-V to 5.5-V V_{CC} Supply**
- **Operates up to 1000 kbit/s**
- **Two Drivers and Two Receivers**
- **Low Standby Current . . . 1 µA Typ**
- **External Capacitors . . . 4 × 0.1 µF**
- **Accepts 5-V Logic Input With 3.3-V Supply**

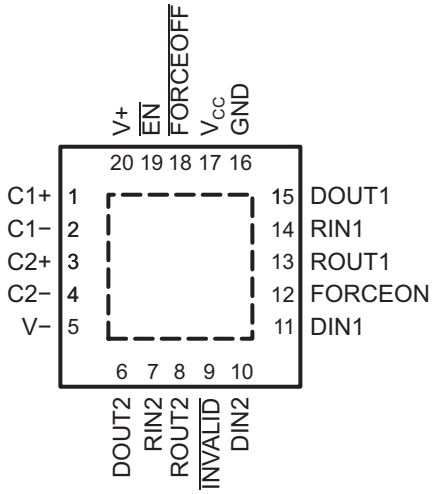
APPLICATIONS

- **Battery-Powered Systems**
- **PDAs**
- **Notebooks**
- **Laptops**
- **Palmtop PCs**
- **Hand-Held Equipment**

DB, DW, OR PW PACKAGE
(TOP VIEW)



RGW PACKAGE
(TOP VIEW)



DESCRIPTION/ ORDERING INFORMATION

The TRSF3223E consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). This device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The TRSF3223E operates at typical data signaling rates up to 1000 kbit/s.

Flexible control options for power management are available when the serial port is inactive. The auto-powerdown feature functions when FORCEON is low and $\overline{\text{FORCEOFF}}$ is high. During this mode of operation, if the device does not sense a valid RS-232 signal, the driver outputs are disabled. If $\overline{\text{FORCEOFF}}$ is set low and EN is high, both drivers and receivers are shut off, and the supply current is reduced to 1 mA. Disconnecting the serial port or turning off the peripheral drivers causes auto-powerdown to occur. Auto-powerdown can be disabled when FORCEON and $\overline{\text{FORCEOFF}}$ are high. With auto-powerdown enabled, the device is automatically activated when a valid signal is applied to any receiver input. The $\overline{\text{INVALID}}$ output is used to notify the user if an RS-232 signal is present at any receiver input. $\overline{\text{INVALID}}$ is high (valid data) if any receiver input voltage is greater than 2.7 V or less than –2.7 V, or has been between –0.3 V and 0.3 V for less than 30 µs. $\overline{\text{INVALID}}$ is low (invalid data) if the receiver input voltage is between –0.3 V and 0.3 V for more than 30 µs. Refer to Figure 4 for receiver input levels.

Table 1. ORDERING INFORMATION

T_A	PACKAGE(1) (2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
0°C to 70°C	SOIC – DW	Tube of 25	TRSF3223ECDW	TRSF3223EC
		Reel of 2000	TRSF3223ECDWR	
	SSOP – DB	Tube of 70	TRSF3223ECDB	RT23EC
		Reel of 2000	TRSF3223ECDBR	
	TSSOP – PW	Tube of 70	TRSF3223ECPW	RT23EC
		Reel of 2000	TRSF3223ECPWR	
–40°C to 85°C	SOIC – DW	Tube of 25	TRSF3223EIDW	TRSF3223EI
		Reel of 2000	TRSF3223EIDWR	
	SSOP – DB	Tube of 70	TRSF3223EIDB	RT23EI
		Reel of 2000	TRSF3223EIDBR	
	TSSOP – PW	Tube of 70	TRSF3223EIPW	RT23EI
		Reel of 2000	TRSF3223EIPWR	
	QFN – RGW	Reel of 3000	TRSF3223EIRGWR	RT23EI

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

FUNCTION TABLES

Each Driver(1)

INPUTS				OUTPUT	DRIVER STATUS
DIN	FORCEON	$\overline{\text{FORCEOFF}}$	VALID RIN RS-232 LEVEL	DOUT	
X	X	L	X	Z	Powered off
L	H	H	X	H	Normal operation with auto-powerdown disabled
H	H	H	X	L	
L	L	H	Yes	H	Normal operation with auto-powerdown enabled
H	L	H	Yes	L	
L	L	H	No	Z	Powered off by auto-powerdown feature
H	L	H	No	Z	

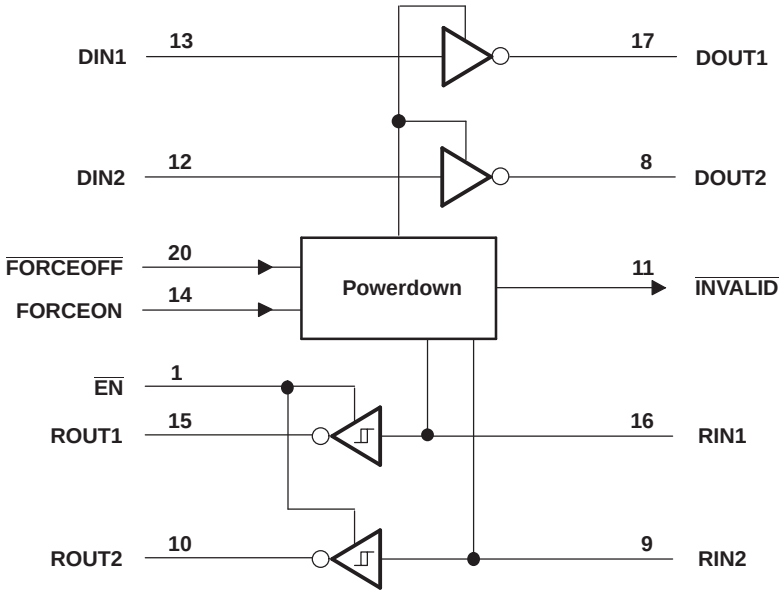
(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Each Receiver[1]

INPUTS			OUTPUT
RIN	$\overline{EN}$	VALID RIN RS-232 LEVEL	ROUT
L	L	X	H
H	L	X	L
X	H	X	Z
Open	L	No	H

(1) H = high level, L = low level, X = irrelevant,
Z = high impedance (off),
Open = input disconnected or connected driver off

LOGIC DIAGRAM (POSITIVE LOGIC)



Pin numbers are for the DB, DW, and PW packages.

Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.3	6	V
V+	Positive-output supply voltage range(2)		–0.3	7	V
V–	Negative-output supply voltage range(2)		0.3	–7	V
V+ – V–	Supply voltage difference(2)			13	V
V_I	Input voltage range	Driver ($\overline{FORCEOFF}$, FORCEON, $\overline{EN}$)	–0.3	6	V
		Receiver	–25	25	
V_O	Output voltage range	Driver	–13.2	13.2	V
		Receiver ($\overline{INVALID}$)	–0.3	V_{CC} + 0.3	
θ_{JA}	Package thermal impedance(3) (4)	DB package		70	°C/W
		DW package		58	
		PW package		83	
T_J	Operating virtual junction temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.
(3) Maximum power dissipation is a function of $T_J(max)$, θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions(1)

See Figure 6

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{EN}$, $\overline{FORCEOFF}$, FORCEON	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{EN}$, $\overline{FORCEOFF}$, FORCEON				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{EN}$, $\overline{FORCEOFF}$, FORCEON		0		5.5	V
	Receiver input voltage			–25		25	
T_A	Operating free-air temperature		TRSF3223EC	0		70	°C
			TRSF3223EI	–40		85	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER			TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
I_I	Input leakage current	$\overline{EN}$, $\overline{FORCEOFF}$, FORCEON			±0.01	±1	µA
I_{CC}	Supply current	Auto-powerdown disabled	V_{CC} = 3.3 V or 5 V, T_A = 25°C, No load, $\overline{FORCEOFF}$ and FORCEON at V_{CC}		0.3	1	mA
		Powered off	No load, $\overline{FORCEOFF}$ at GND		1	10	µA
		Auto-powerdown enabled	No load, $\overline{FORCEOFF}$ at V_{CC}, FORCEON at GND, All RIN are open or grounded		1	10	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

DRIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND	–5	–5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$		±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND		±0.01	±1	µA
I_{OS}	Short-circuit output current(3)	V_{CC} = 3.6 V, V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V, V_O = 0 V				
r_o	Output resistance	V_{CC}, V+, and V– = 0 V, V_O = ±2 V	300	10M		Ω
I_{OZ}	Output leakage current	$\overline{FORCEOFF}$ = GND, V_{CC} = 3 V to 3.6 V, V_O = ±12 V			±25	µA
		$\overline{FORCEOFF}$ = GND, V_{CC} = 4.5 V to 5.5 V, V_O = ±12 V			±25	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Switching Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS			MIN	TYP(2)	MAX	UNIT
	Maximum data rate (see Figure 1)	R_L = 3 kΩ, One DOUT switching	C_L = 1000 pF		250			kbit/s
			C_L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000			
			C_L = 1000 pF,	V_{CC} = 4.5 V to 5.5 V	1000			
$t_{sk(p)}$	Pulse skew(3)	C_L = 150 pF to 2500 pF,	R_L = 3 kΩ to 7 kΩ,	See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	R_L = 7 kΩ,	C_L = 150 pF to 1000 pF		8		90	V/µs
		R_L = 3 kΩ	C_L = 1000 pF		12		60	
			C_L = 150 pF to 250 pF		24		150	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

RECEIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1 mA	V_{CC} – 0.6	V_{CC} – 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.6	2.4	V
		V_{CC} = 5 V		1.9	2.4	
$V_{IT–}$	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.1		V
		V_{CC} = 5 V	0.6	1.4		
V_{hys}	Input hysteresis (V_{IT+} – $V_{IT–}$)			0.5		V
I_{OZ}	Output leakage current	$\overline{EN}$ = V_{CC}		±0.05		µA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5		kΩ

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TYP(2)	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See Figure 3	150	ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L = 150 pF, See Figure 3	150	ns
t_{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
t_{dis}	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
$t_{sk(p)}$	Pulse skew(3)	See Figure 3	50	ns

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

AUTO-POWERDOWN SECTION

Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
$V_{T+(valid)}$	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	$\overline{FORCEOFF}$ = V_{CC}		2.7	V
$V_{T-(valid)}$	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	$\overline{FORCEOFF}$ = V_{CC}	–2.7		V
$V_{T(invalid)}$	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND,	$\overline{FORCEOFF}$ = V_{CC}	–0.3	0.3	V
V_{OH}	$\overline{INVALID}$ high-level output voltage	I_{OH} = 1 mA, $\overline{FORCEOFF}$ = V_{CC}	FORCEON = GND,	V_{CC} – 0.6		V
V_{OL}	$\overline{INVALID}$ low-level output voltage	I_{OL} = 1.6 mA, $\overline{FORCEOFF}$ = V_{CC}	FORCEON = GND,		0.4	V

Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

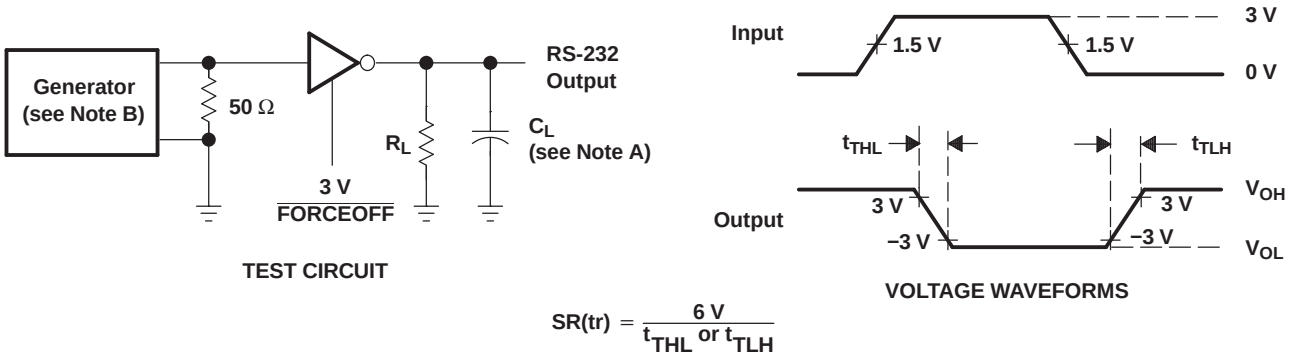
PARAMETER		TYP(1)	UNIT
t_{valid}	Propagation delay time, low- to high-level output	1	µs
$t_{invalid}$	Propagation delay time, high- to low-level output	30	µs
t_{en}	Supply enable time	100	µs

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.



$$SR(tr) = \frac{6\ V}{t_{THL} \text{ or } t_{TLH}}$$

Figure 1. Driver Slew Rate

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

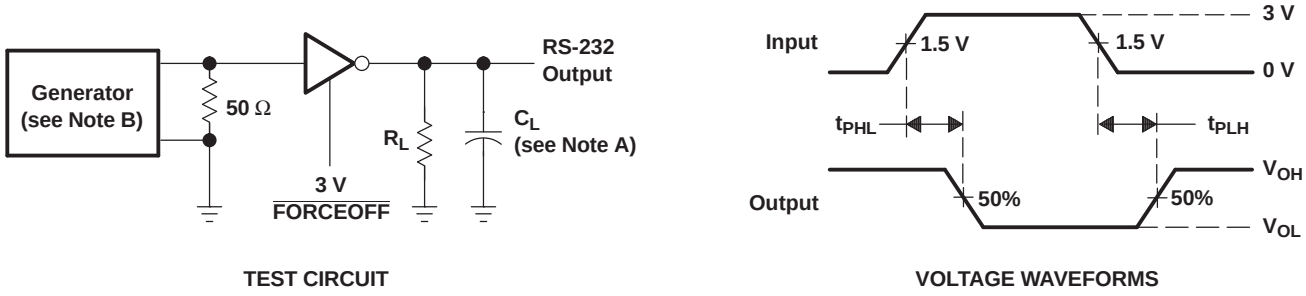


Figure 2. Driver Pulse Skew

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

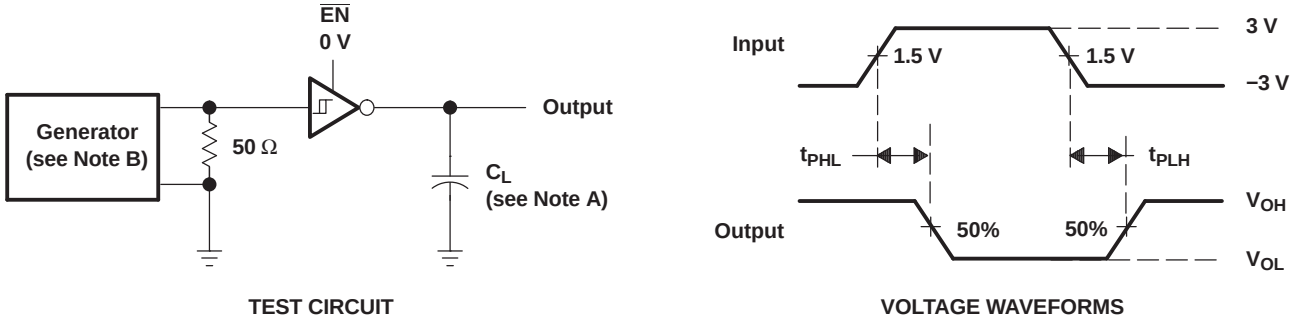


Figure 3. Receiver Propagation Delay Times

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

PARAMETER MEASUREMENT INFORMATION (continued)

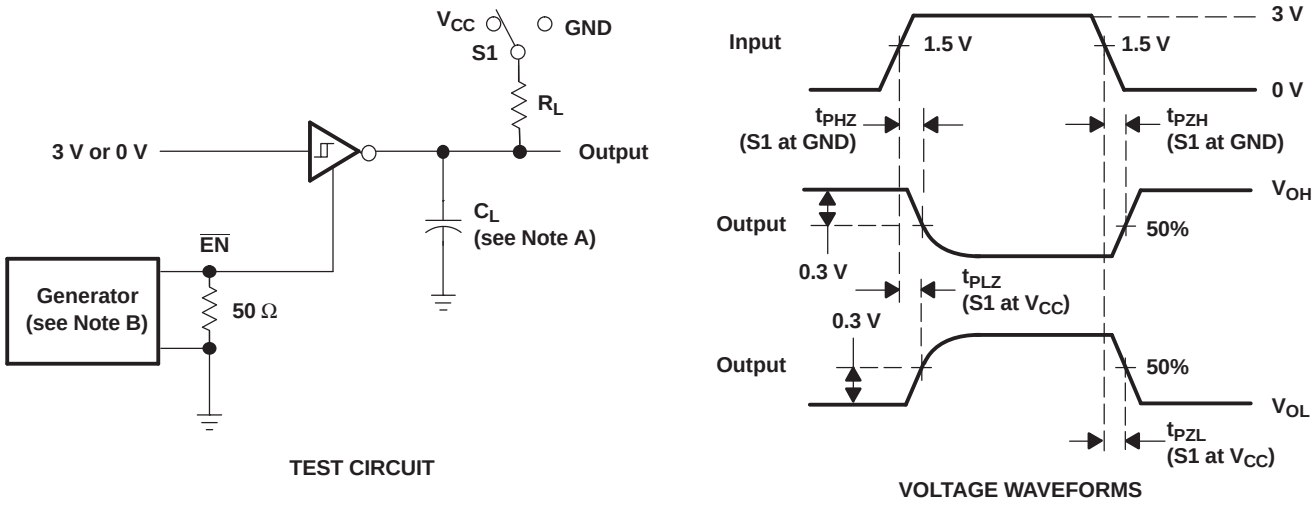
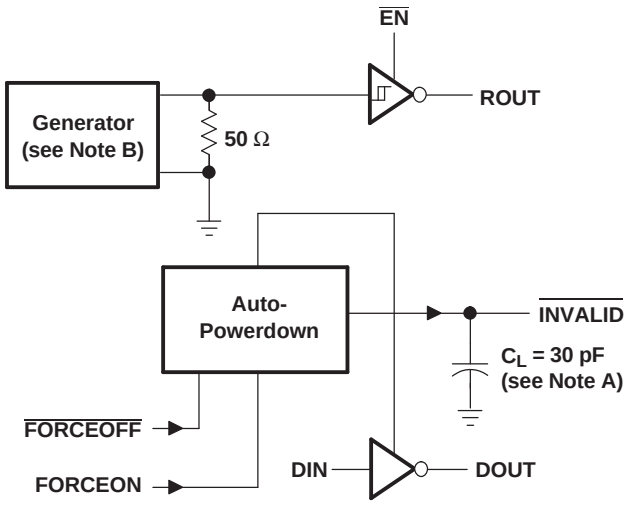


Figure 4. Receiver Enable and Disable Times

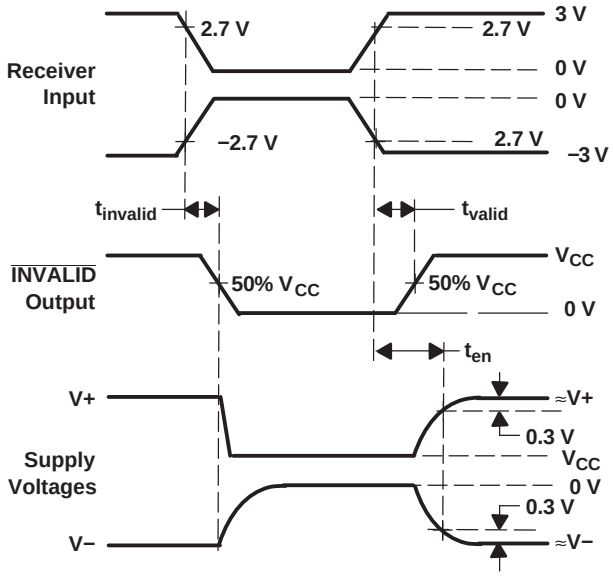
A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns.

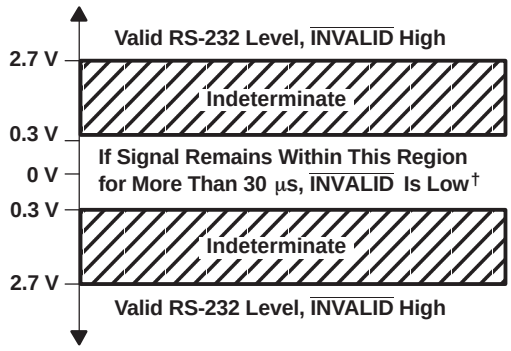
PARAMETER MEASUREMENT INFORMATION (continued)



TEST CIRCUIT



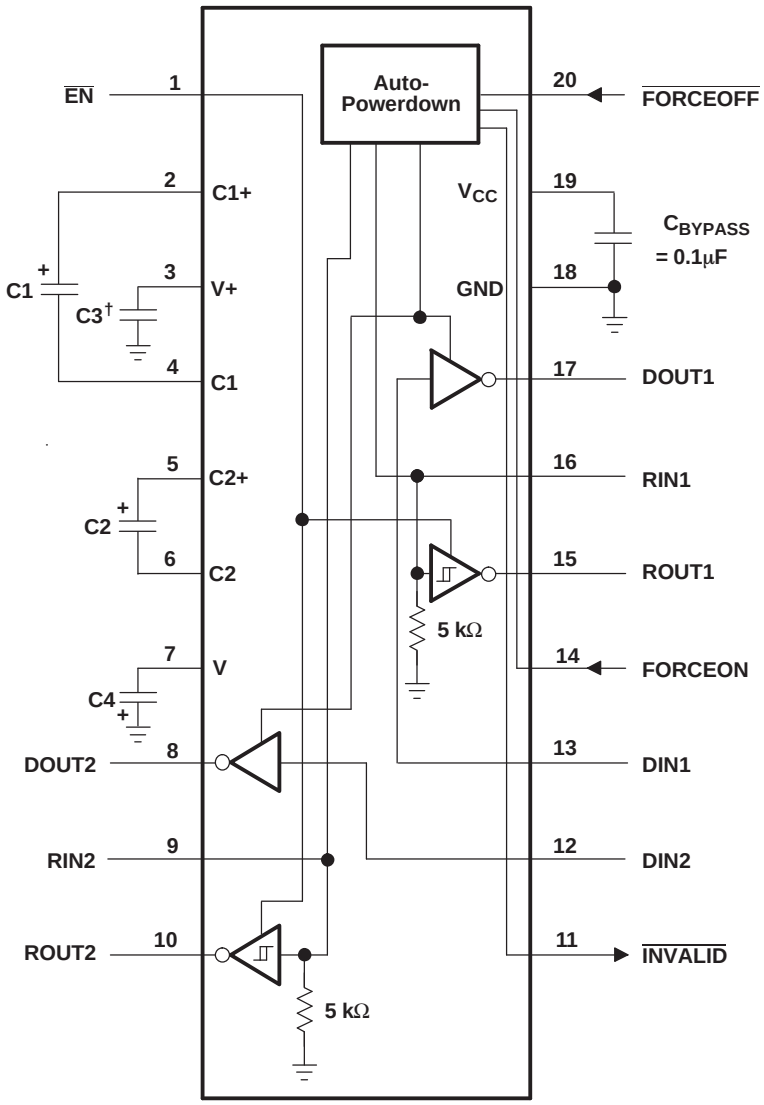
VOLTAGE WAVEFORMS



† Auto-powerdown disables drivers and reduces supply current to 1 μA

Figure 5. INVALID Propagation Delay Times and Supply Enabling Time

APPLICATION INFORMATION



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 μF	0.1 μF
5 V ± 0.5 V	0.047 μF	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μF

Figure 6. Typical Operating Circuit and Capacitor Values

REVISION HISTORY

Changes from Original (August 2007) to Revision A	Page
• Added RGW package to datasheet.	1
• Deleted RHL package from datasheet.	1

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/ Ball Finish	MSL Peak Temp (3)	Samples (Requires Login)
TRSF3223ECDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDBG4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDBRG4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECDWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223ECPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDBG4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDBRG4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/ Ball Finish	MSL Peak Temp (3)	Samples (Requires Login)
TRSF3223EIDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIDWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TRSF3223EIRGWR	ACTIVE	VQFN	RGW	20	3000	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

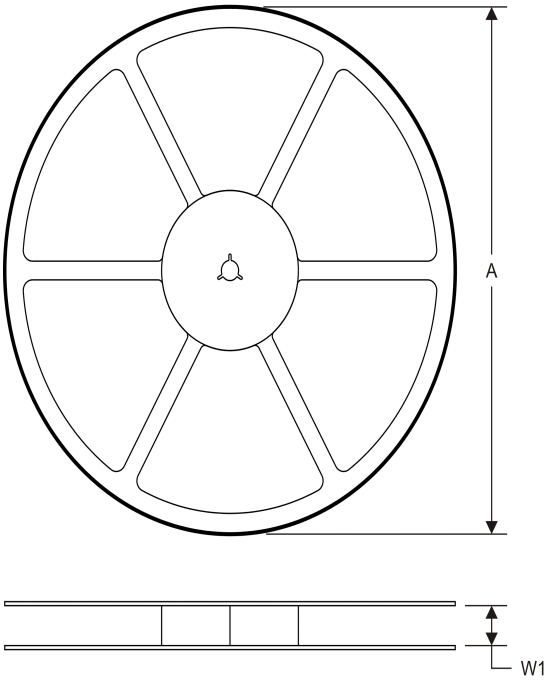
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

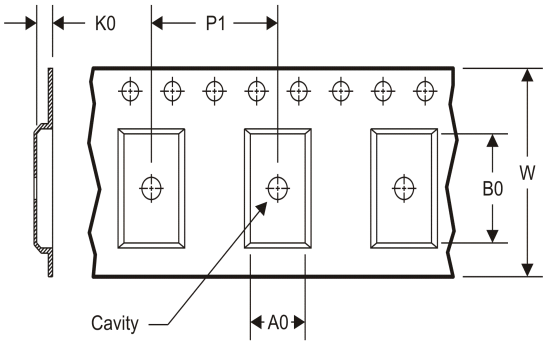
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



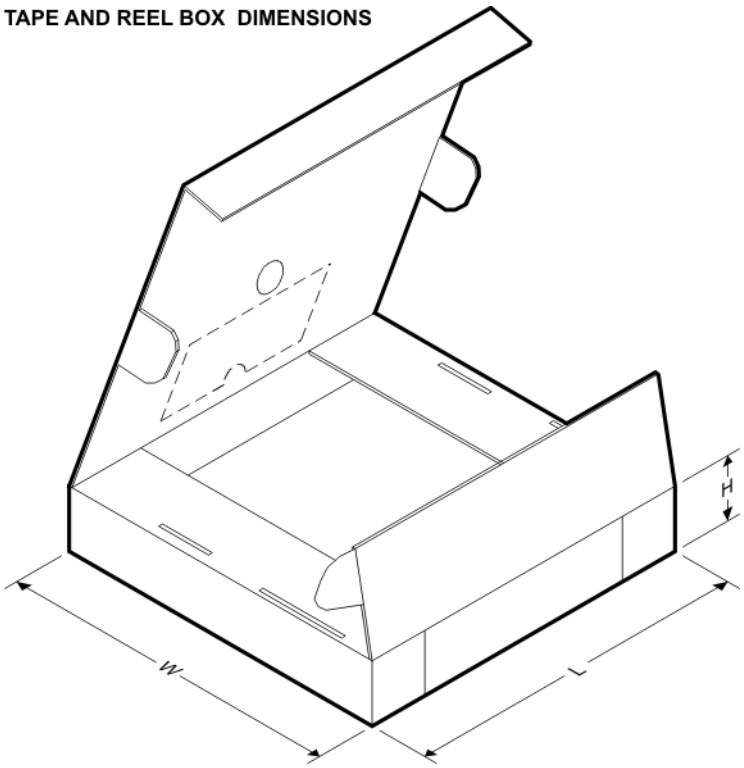
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRSF3223ECDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
TRSF3223ECDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
TRSF3223ECPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
TRSF3223EIDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
TRSF3223EIDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
TRSF3223EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
TRSF3223EIRGWR	VQFN	RGW	20	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

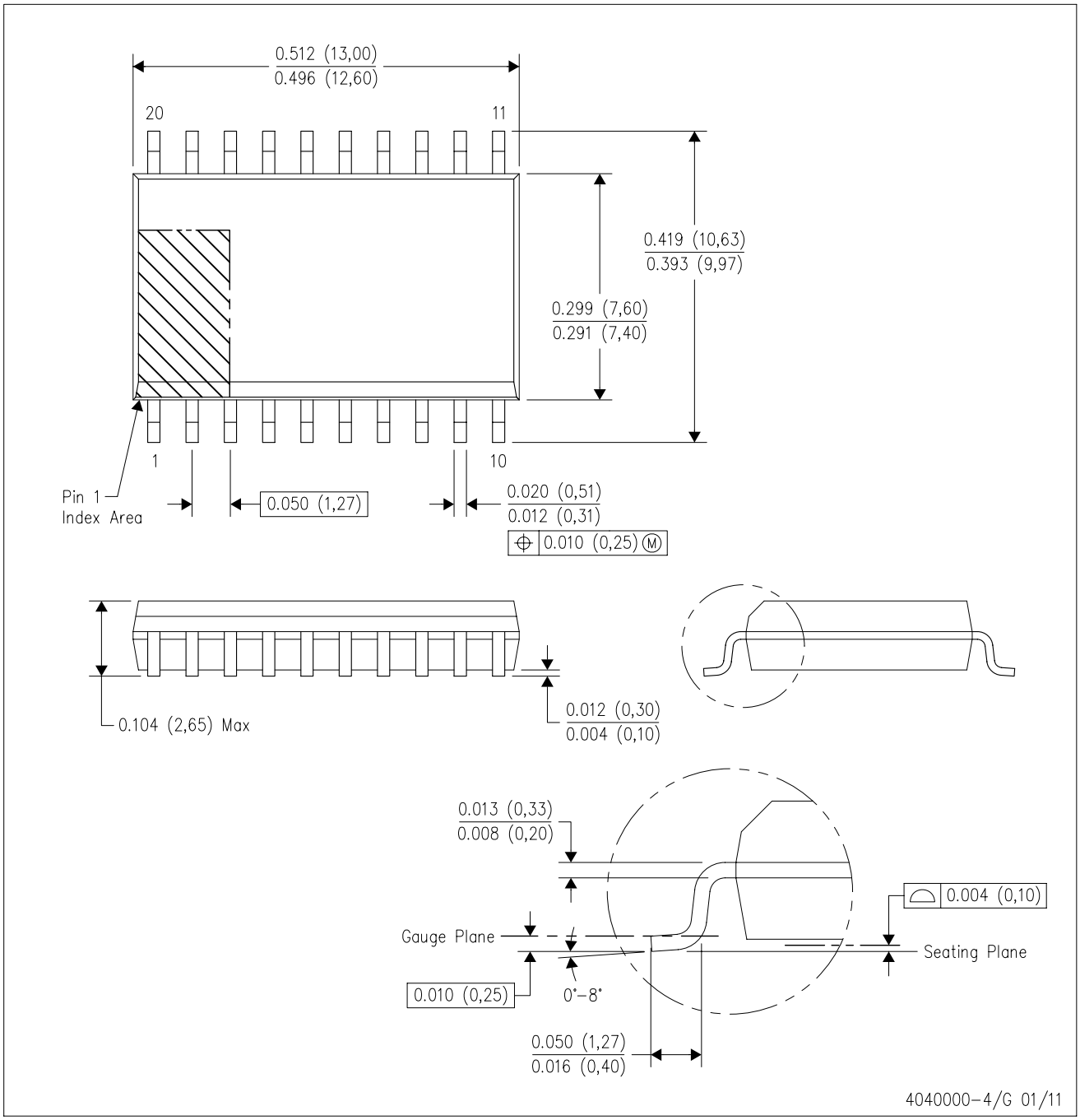
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

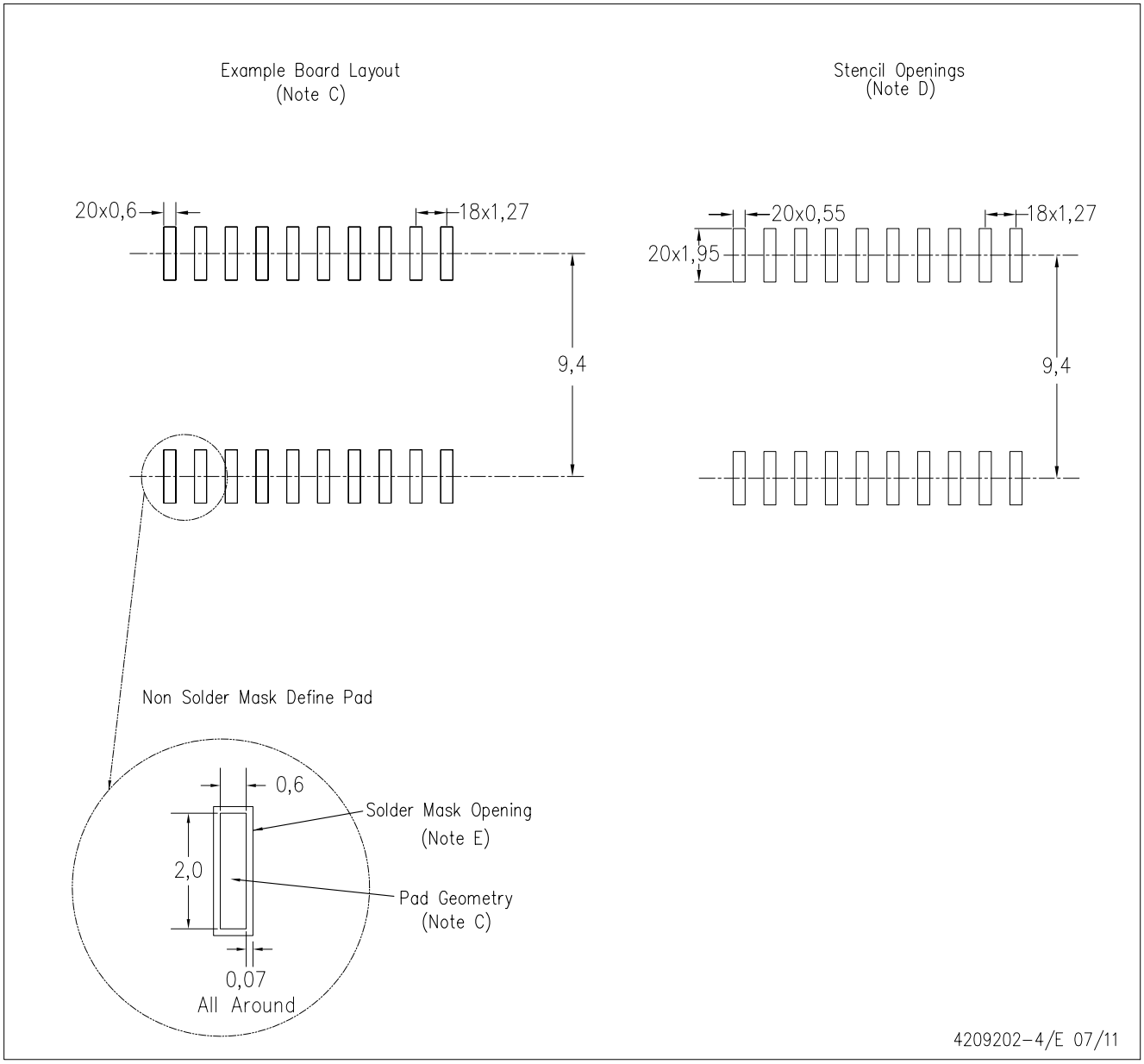
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRSF3223ECDBR	SSOP	DB	20	2000	367.0	367.0	38.0
TRSF3223ECDWR	SOIC	DW	20	2000	367.0	367.0	45.0
TRSF3223ECPWR	TSSOP	PW	20	2000	367.0	367.0	38.0
TRSF3223EIDBR	SSOP	DB	20	2000	367.0	367.0	38.0
TRSF3223EIDWR	SOIC	DW	20	2000	367.0	367.0	45.0
TRSF3223EIPWR	TSSOP	PW	20	2000	367.0	367.0	38.0
TRSF3223EIRGWR	VQFN	RGW	20	3000	367.0	367.0	35.0

DW (R–PDSO–G20) PLASTIC SMALL OUTLINE



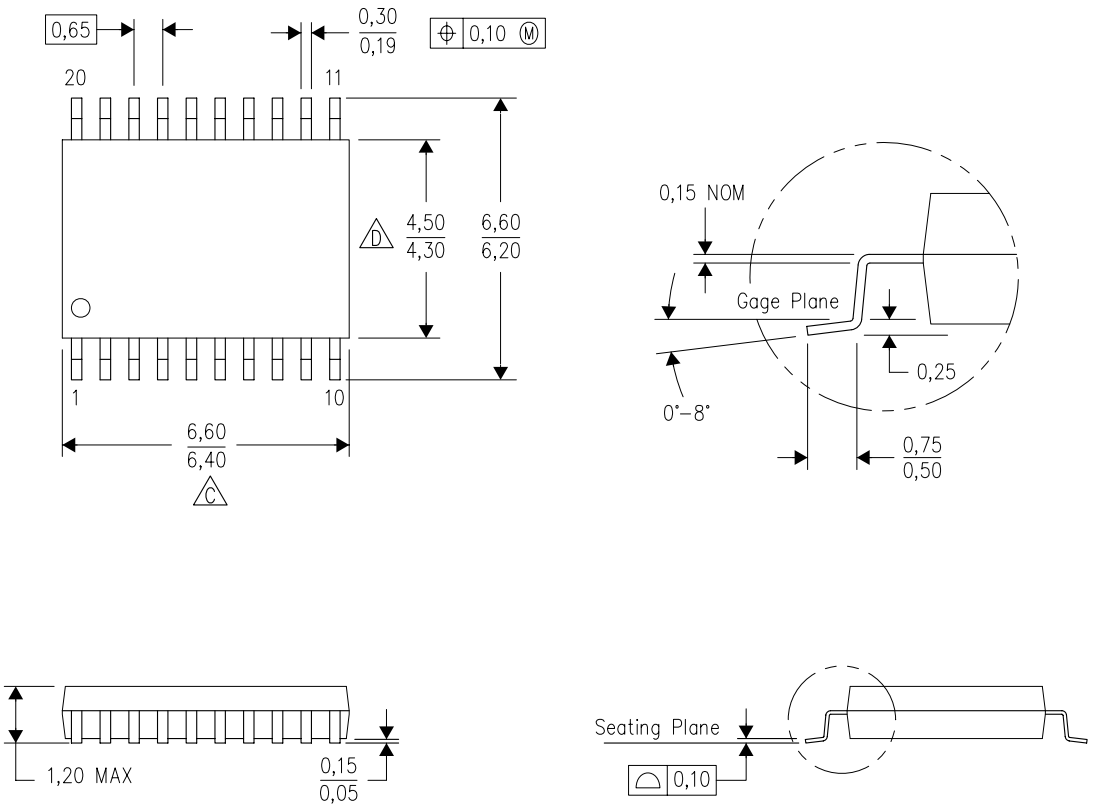
NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AC.

DW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

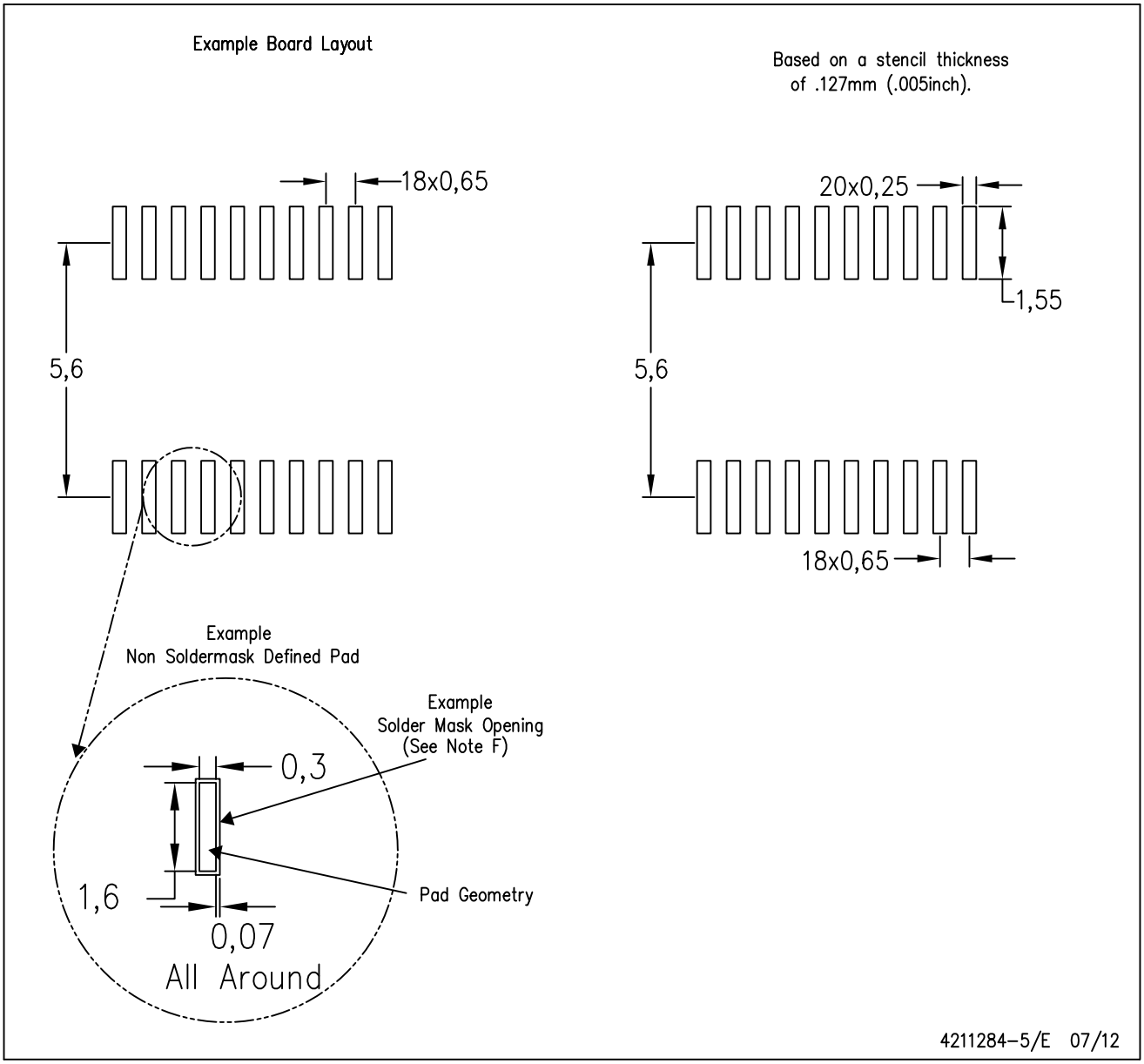
PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



4040064–5/G 02/11

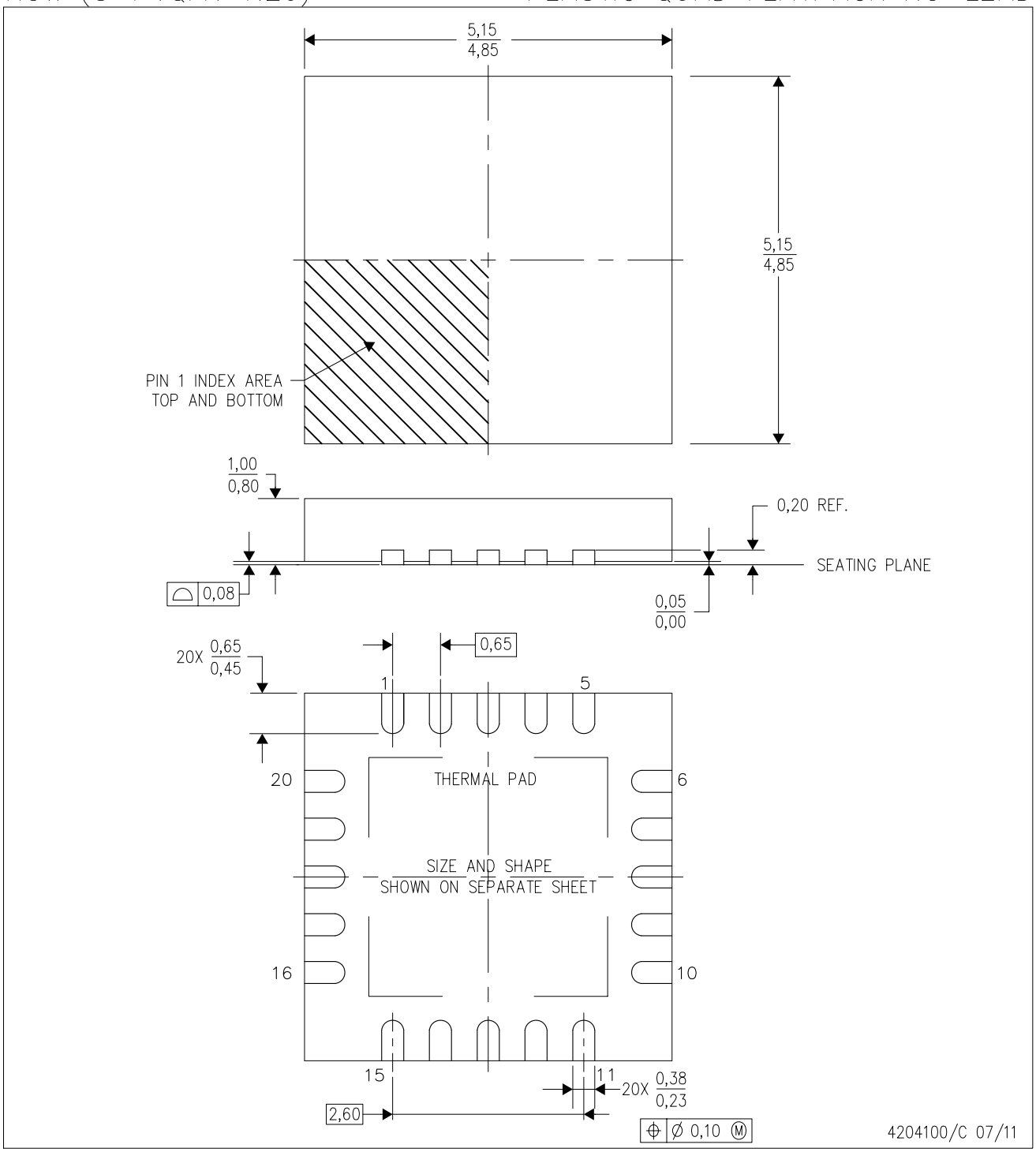
NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

RGW (S–PVQFN–N20) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5–1994.
B. This drawing is subject to change without notice.
C. Quad Flat pack, No–leads (QFN) package configuration
D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
F. Falls within JEDEC MO–220.

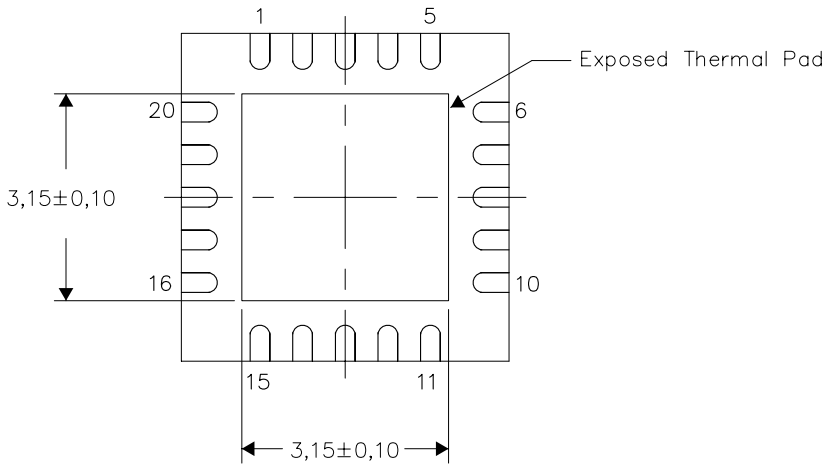
RGW (S–PVQFN–N20) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



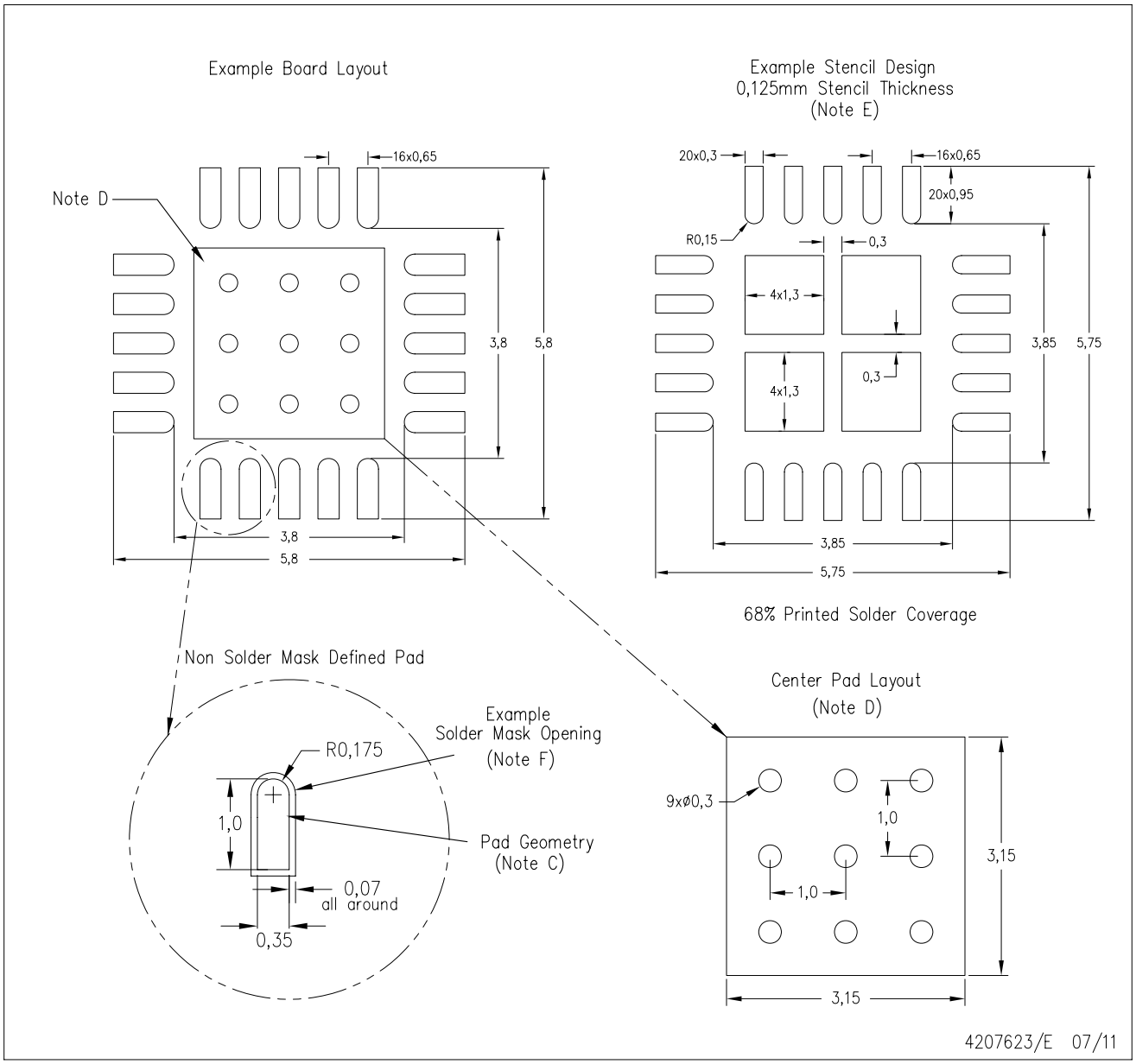
Bottom View

Exposed Thermal Pad Dimensions

4206352–2/J 07/11

NOTE: All linear dimensions are in millimeters

RGW (S–PVQFN–N20) PLASTIC QUAD FLATPACK NO–LEAD



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, QFN Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
F. Customers should contact their board fabrication site for solder mask tolerances.

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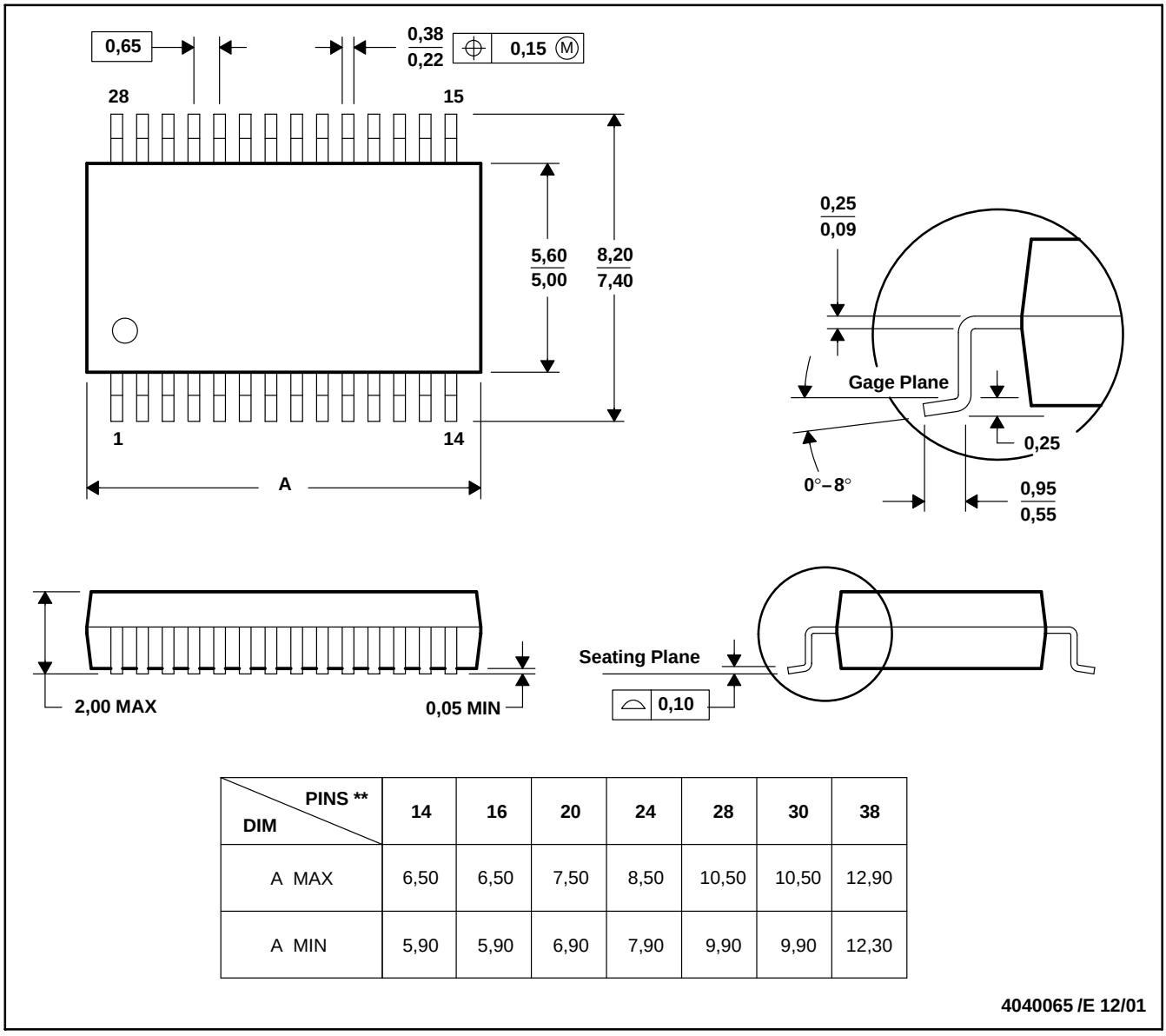
DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

28 PINS SHOWN



DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 /E 12/01

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

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